

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 112857-315	Application No. 10/062,776
	Applicant Yoshiyuki Yanagisawa et al.	
	Filing Date 01/30/2002	Group 2812

U.S. PATENT DOCUMENTS						
Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate
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Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation		
						Yes	No	
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JS	06-504139	05/12/1994	Japan					
Examiner: JS				Date Considered: 3/11/04				
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						Yes	No
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						Yes	No	
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S	Zheleva et al., "Pendeo/Epitaxy - A New Approach For Lateral Growth Of Gallium Nitride Structures", MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).
S	Kapolnek et al., "Spatial Control Of InGaN Luminescence By MOCVD Selective Epitaxy, Journal Of Crystal Growth", 189/190 (1998) pp. 83/86.
S	Applied Physics Letters, Vol. 76, Number 22, 29 May 2000, "Selective Growth Of InGaN Quantum Dot Structures And Their Microphotoluminescence At Room Temperature", Tachibani et al, pages 3212/3214

Examiner: <u>S. [Signature]</u>	Date Considered: <u>3/11/04</u>
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